



ELECTRONICS, INC.
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NTE56 Silicon NPN Transistor High Gain Switch and Pass Regulator

Absolute Maximum Ratings:

Collector–Emitter Voltage, V_{CEO}	80V
Collector–Base Voltage, V_{CB}	100V
Emitter–Base Voltage, V_{EB}	6V
Collector Current, I_C	3A
Base Current, I_B	1A
Total Power Dissipation ($T_C = +25^\circ\text{C}$), P_D	30W
Junction Temperature, T_J	+150°C
Storage Temperature Range, T_{stg}	–55° to +150°C

Electrical Characteristics: ($T_C = +25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector Cutoff Current	I_{CBO}	$V_{CB} = 100V$	–	–	10	μA
Emitter Cutoff Current	I_{EBO}	$V_{EB} = 6V$	–	–	100	μA
Collector–Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C = 25\text{mA}$	80	–	–	V
DC Current Gain	h_{FE}	$V_{CE} = 4V, I_C = 0.5A$	500	–	–	
Collector–Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = 2A, I_B = 50\text{mA}$	–	–	0.5	V
Current Gain–Bandwidth Product	f_T	$V_{CE} = 12V, I_E = -0.2A$	–	15	–	MHz

